| Part Number Customer | | | | | |
|----------------------|-----------|---|-----------------------------------|----------------------------------|--|
| Category | Parameter | | Specification | Measurement Method | |
| OverallWafer | 1.0 | Diameter | 150.00 +/- 0.50 mm | | |
| | 2.0 | Primary Flat Orientation | {110} +/-1 degree | Customer supplied material | |
| | 3.0 | Primary Flat Length | 57.50 +/- 2.50 mm | Customer supplied material | |
| | 4.0 | Secondary Flat Orientation | none | Customer supplied material | |
| | 5.0 | Overall Thickness | 611.00 +/- 11.00 μm | ADE, 100% | |
| | 6.0 | Total Thickness Variation (TTV) | <2.00µm | Guaranteed by Process | |
| | 7.0 | Bow | <60.00µm | ADE to ASTM F534, 100% | |
| | 8.0 | Warp | <60.00µm | ADE to ASTM F534, 100% | |
| | 9.0 | Edge Chips | 0 | Bright Light, 100% | |
| | 10.0 | Edge Exclusion | 5mm | | |
| HandleSilicon | 11.0 | Handle Growth Method | CZ | Customer supplied material | |
| | 12.0 | Handle Orientation | {100} +/- 0.5 degree | Customer supplied material | |
| | 13.0 | Handle Thickness | 600.00 +/- 10.00 μm | ADE, 100% | |
| | 14.0 | Handle Doping Type | N | Customer supplied material | |
| | 15.0 | Handle Dopant | Phosphorous | Customer supplied material | |
| | 16.0 | Handle Resistivity | 1~10 Ohmcm | Customer supplied material | |
| | 17.0 | Backside Finish | Polished with oxide and lasermark | Guaranteed by process | |
| BuriedOxide | 18.0 | Oxide Type | Thermal | | |
| | 19.0 | Oxide Thickness | 10,000.00 +/- 500.00 A | Nanospec centre point, 4% | |
| | 20.0 | Oxide formed on | Handle | | |
| DeviceSilicon | 21.0 | Device Growth Method | CZ | Customer supplied material | |
| | 22.0 | Device Orientation | {100} +/- 0.5 degree | Customer supplied material | |
| | 23.0 | Nominal Thickness | 10.00 +/- 0.50 μm | Filmetrics 9pts, 100% (note3) | |
| | 24.0 | Distance to device silicon edge from wafer edge | < 2mm | Typical by Process | |
| | 25.0 | Device Doping Type | Ν | Customer supplied material | |
| | 26.0 | Device Dopant | Phosphorous | Customer supplied material | |
| | 27.0 | Device Resistivity | 1~10 Ohmcm | Customer supplied material | |
| | 28.0 | Surface Voids | None | Bright Light, 100% (note2) | |
| | 29.0 | Haze | None | Bright Light, 100% (note2) | |
| | 30.0 | Scratches | none on the front-side | Bright Light, 100% (note2) | |

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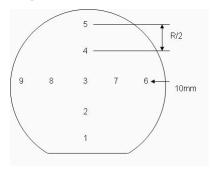
Product Specification

1000.714101

| Part Number | | Customer | | |
|-------------------|--|---|--------------------|--|
| Category | Parameter | Specification | Measurement Method | |
| Shipping Details | ails Wafer per box : Max 25 | | | |
| | Packaging : | Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging | | |
| | Lot Shipment Data | Device Thickness Bow / Warp Data Handle and SOI Thickness | | |
| Explanatory Notes | 1. Microscope inspection performed using microscope scan as below. 5x objective. | | | |

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information